

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS) SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

HN3B01F

AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS.

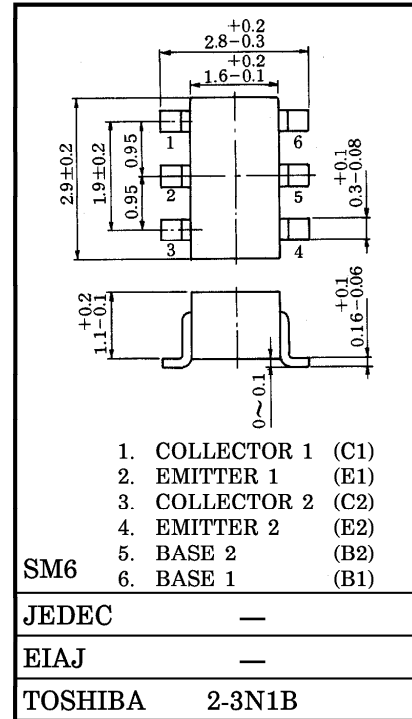
Unit in mm

Q1:

- High Voltage and High Current
: $V_{CEO} = 50V$, $I_C = 150mA$ (Max.)
- High h_{FE} : $h_{FE} = 120 \sim 400$
- Excellent h_{FE} Linearity
: $h_{FE}(I_C = 0.1mA) / h_{FE}(I_C = 2mA) = 0.95$ (Typ.)

Q2:

- High Voltage and High Current
: $V_{CEO} = -50V$, $I_C = -150mA$ (Max.)
- High h_{FE} : $h_{FE} = 120 \sim 400$
- Excellent h_{FE} Linearity
: $h_{FE}(I_C = -0.1mA) / h_{FE}(I_C = -2mA) = 0.95$ (Typ.)



Weight : 0.015g

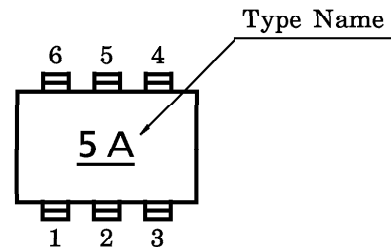
Q1 MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA

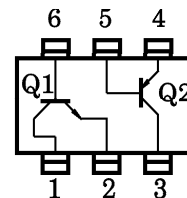
Q2 MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Base Current	I_B	-30	mA

MARKING



EQUIVALENT CIRCUIT (TOP VIEW)



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● The information contained herein is subject to change without notice.

Q1, Q2 COMMON MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	PC*	300	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	Tstg	-55~125	°C

* Total Rating

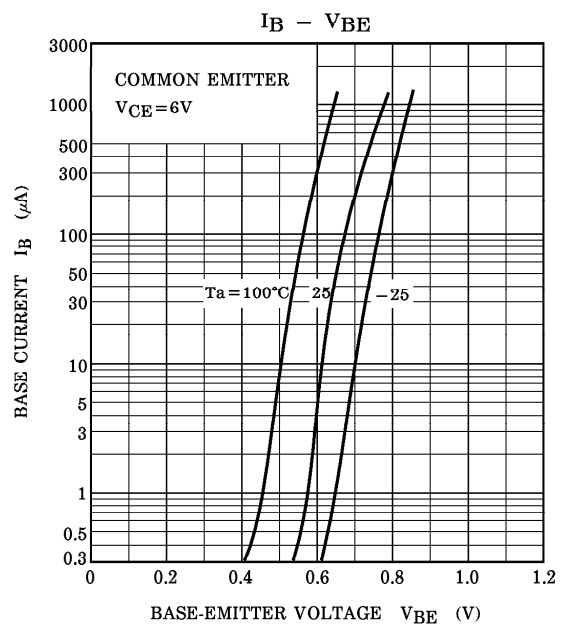
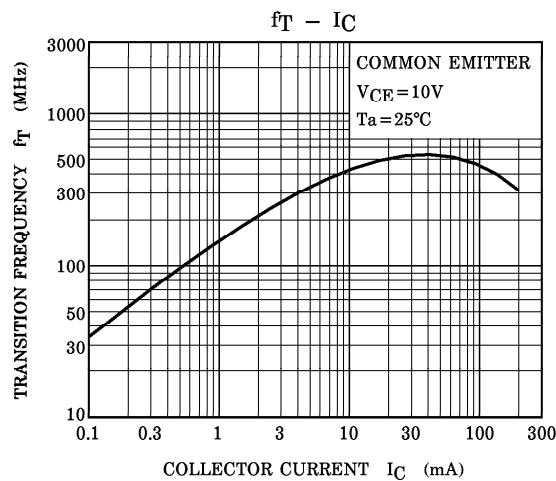
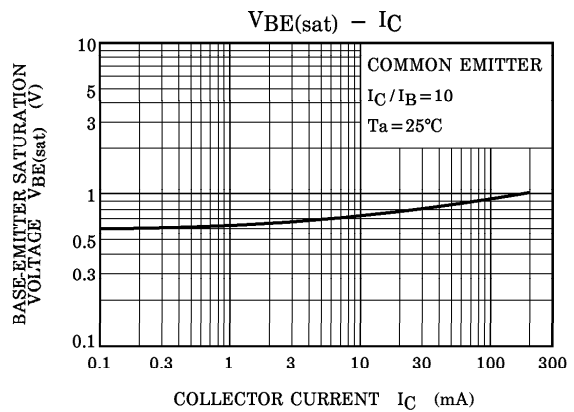
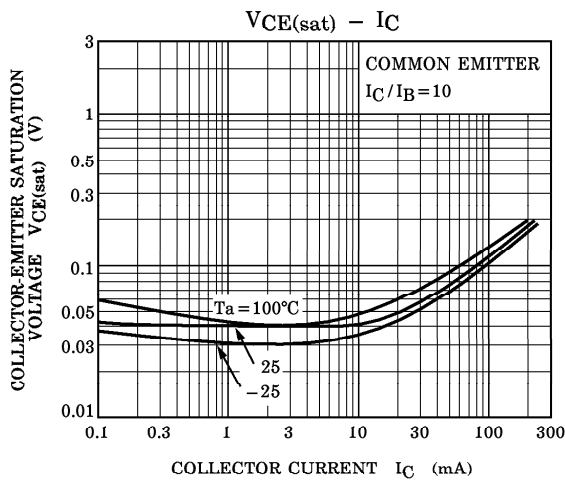
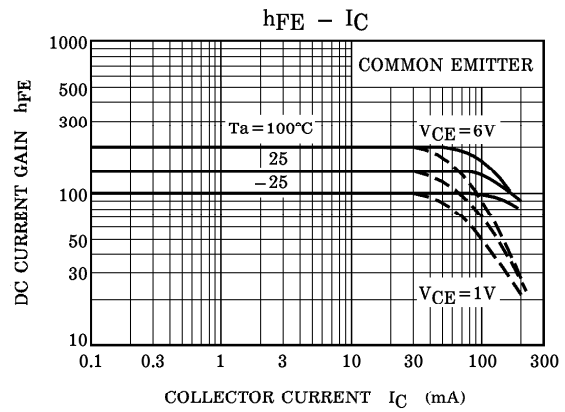
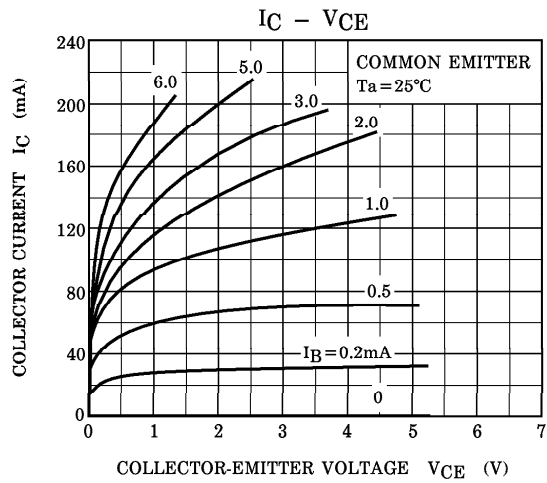
Q1 ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} = 60V, I _E = 0	—	—	0.1	μA
Emitter Cut-off Current	IEBO	V _{EB} = 5V, I _C = 0	—	—	0.1	μA
DC Current Gain	h _{FE}	V _{CE} = 6V, I _C = 2mA	120	—	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 100mA, I _B = 10mA	—	0.1	0.25	V
Transition Frequency	f _T	V _{CE} = 10V, I _C = 1mA	—	150	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0 f = 1MHz	—	2	—	pF

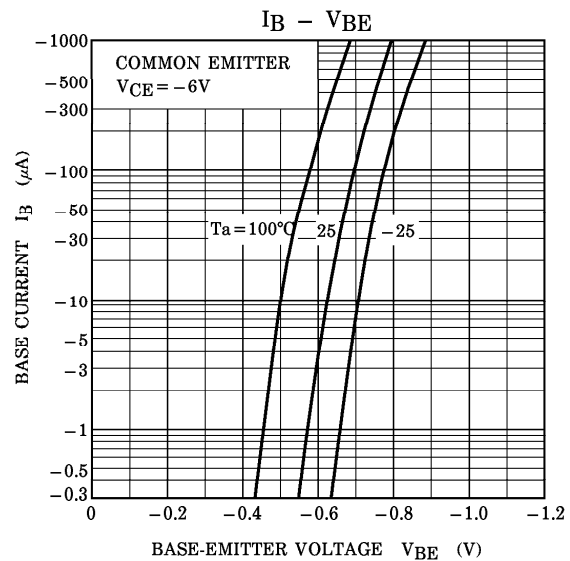
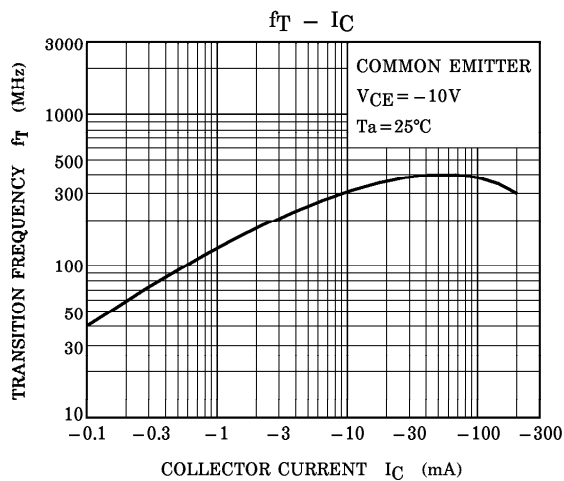
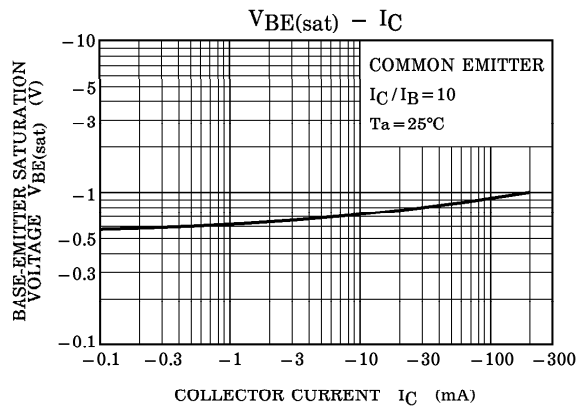
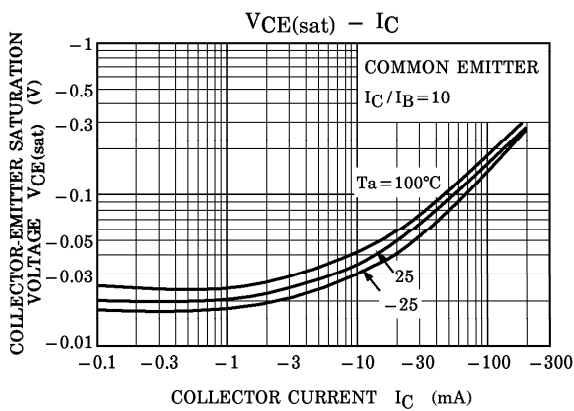
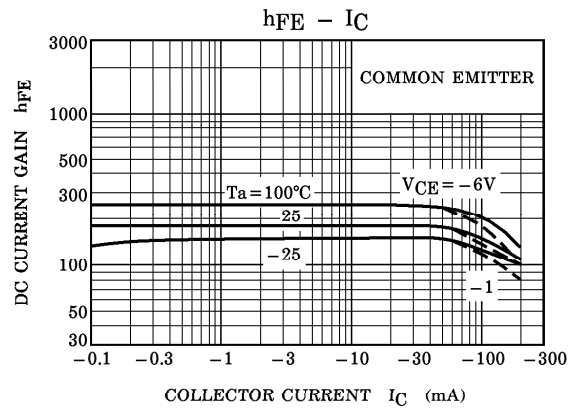
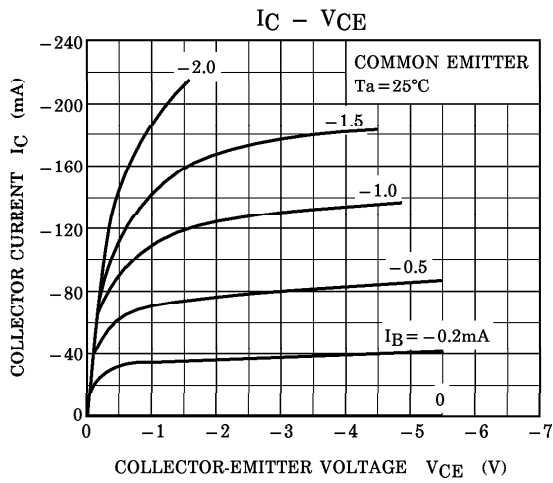
Q2 ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} = -50V, I _E = 0	—	—	-0.1	μA
Emitter Cut-off Current	IEBO	V _{EB} = -5V, I _C = 0	—	—	-0.1	μA
DC Current Gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	120	—	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA	—	-0.1	-0.3	V
Transition Frequency	f _T	V _{CE} = -10V, I _C = -1mA	—	120	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0 f = 1MHz	—	4	—	pF

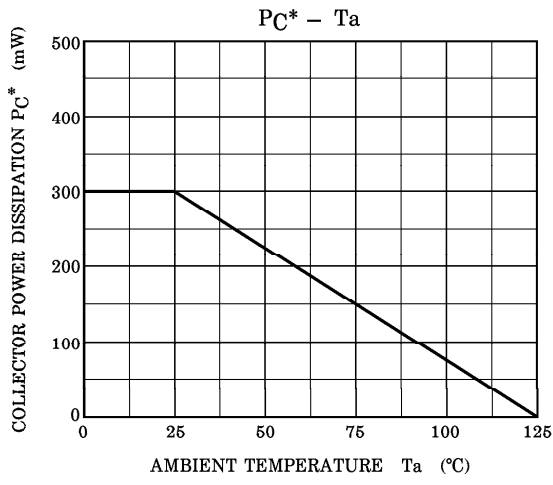
Q1 (NPN TRANSISTOR)



Q2 (PNP TRANSISTOR)



(Q1, Q2 COMMON)



*: Total Rating